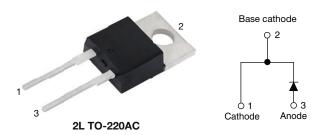
# Vishay Semiconductors

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Hyperfast Rectifier, 30 A FRED Pt<sup>®</sup> G5



### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	30 A			
V <sub>R</sub>	600 V			
V <sub>F</sub> at I <sub>F</sub> at 125 °C	1.15 V			
t <sub>rr</sub> (typ.)	25 ns			
T <sub>J</sub> max.	175 °C			
Package	2L TO-220AC			
Circuit configuration	Single			

#### FEATURES

- Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV battery charging stations and high frequency stages of UPS applications.

### **MECHANICAL DATA**

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Repetitive peak reverse voltage	V <sub>RRM</sub>		600	V	
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 113 °C, D = 0.50	30	А	
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 113 °C, D = 0.50, f = 20 kHz	60		
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{C}$ = 25 °C, $t_{p}$ = 10 ms, sine wave	330		
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 30 A	-	1.3	1.6	V
Forward voltage		I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C	-	1.15	-	
Povoroo lookogo ourront	I	$V_{R} = V_{R}$ rated	-	-	20	
Reverse leakage current I <sub>R</sub>		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA
Junction capacitance	C <sub>T</sub> V <sub>R</sub> = 200 V		-	36	-	pF
Series inductance	L <sub>S</sub>	L <sub>S</sub> Measured to lead 5 mm from package bod		8	-	nH

 Revision: 29-Sep-2020
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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		I <sub>F</sub> = 1.0 A,dI <sub>F</sub> /dt =	$I_F = 1.0 \text{ A,d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		25	-	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	41	-	ns
		T <sub>J</sub> = 125 °C		-	58	-	
Peak recovery current		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 20 A dI <sub>F</sub> /dt = 1000 A/μs V <sub>B</sub> = 400 V	-	19	-	A
Feak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	32	-	
	0	T <sub>J</sub> = 25 °C	n	-	419	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	1176	-	
Deverse receiver time		T <sub>J</sub> = 25 °C		-	46	-	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	65	-	ns
Deels receivers europt		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 30 A dI <sub>F</sub> /dt = 1000 A/μs V <sub>R</sub> = 400 V	-	21	-	A
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	36	-	
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C		-	550	-	nC
	T <sub>J</sub> = 125 °C	]	-	1560	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.3	°C/W
Weight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Marking device		Case style 2L TO-220AC		E5TH	13006	

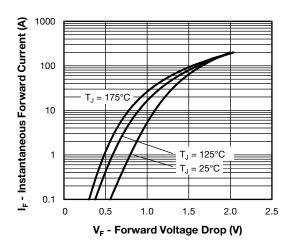


Fig. 1 - Forward Voltage Drop Characteristics, Per Leg

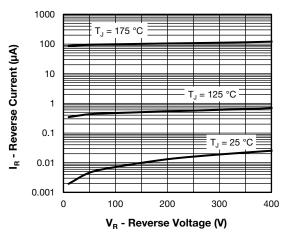
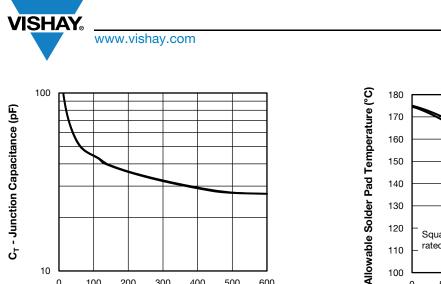


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage, Per Leg



# DC 140 130 120 Square wave (D = 0.50)rated V<sub>R</sub> applied 110

VS-E5TH3006-M3

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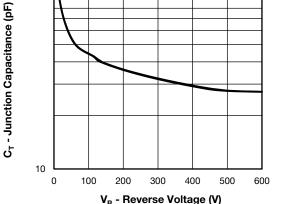


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, Per Leg



20

25

30

35

15

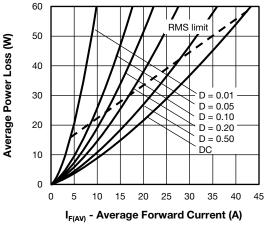


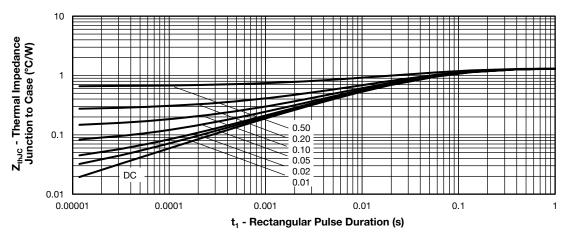
Fig. 5 - Forward Power Loss Characteristics, Per Leg

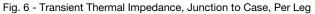
100

0

5

10



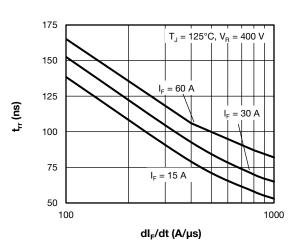


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Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt, Per Leg

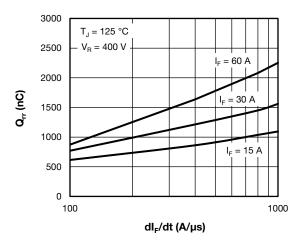


Fig. 8 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt, Per Leg

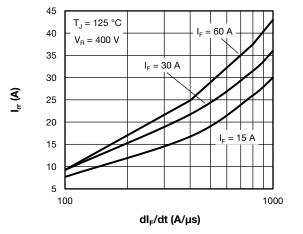


Fig. 9 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt, Per Leg

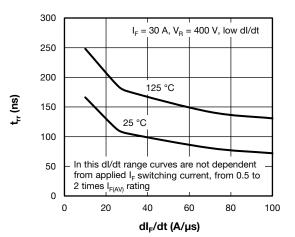


Fig. 10 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt, Per Leg

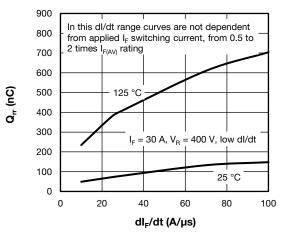


Fig. 11 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt, Per Leg

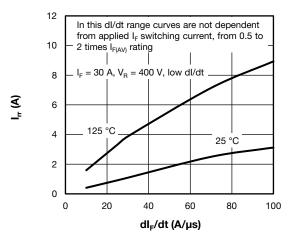


Fig. 12 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt, Per Leg

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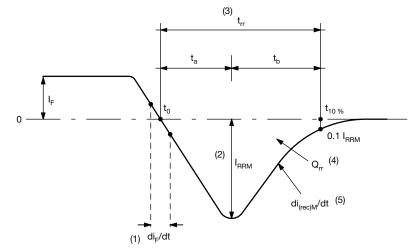


Fig. 13 - Reverse Recovery Waveform and Definitions

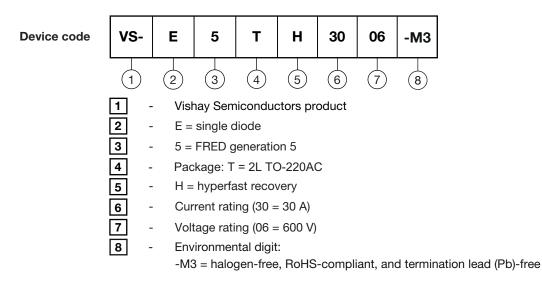
#### Notes

- <sup>(1)</sup> di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- $^{(3)}$  t<sub>rr</sub> reverse recovery time measured from t<sub>0</sub>, crossing point of negative going I<sub>F</sub>, to point t<sub>10%</sub>, 0.1 I<sub>RRM</sub>
- $^{(4)}~~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

#### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-E5TH3006-M3	50	1000	Antistatic plastic tube		

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?96156				
Part marking information	www.vishay.com/doc?95391			

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